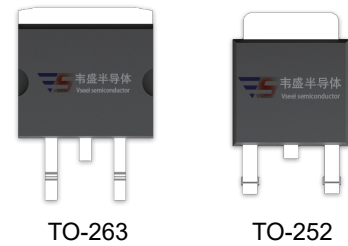
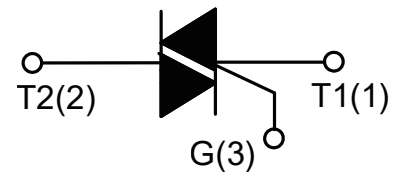


DESCRIPTION:

The T405Q-600B SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	600/800	V


ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)		V_{DRM}	600/800	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)		V_{RRM}	600/800	V
RMS on-state current	TO-252 ($T_C=100^\circ\text{C}$)	$I_{T(RMS)}$	4	A
	TO-263 ($T_C=95^\circ\text{C}$)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	35	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	6.1	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	I - II - III	di/dt	50	$\text{A}/\mu\text{s}$
	IV		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				T	D	E	F	
I_{GT}	$V_D=12V$	I - II - III	MAX	5	5	10	25	mA
		IV		5	10	25	70	
V_{GT}		ALL	MAX	1.3				V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3K\Omega$	ALL	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I - III	MAX	10	20	30	40	mA
		II - IV		15	35	45	60	
I_H	$I_T=100\text{mA}$		MAX	5	15	25	30	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	20	50	100	150	V/ μs
(dV/dt) _c	(dI/dt) _c =1.7A/ms $T_j=125^\circ\text{C}$		MIN	0.1	0.1	0.5	5	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=5.5A$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.6	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252 2.8		$^\circ\text{C/W}$
		TO-263	3.8	
$R_{th(j-a)}$	junction to ambient	TO-252 70		$^\circ\text{C/W}$
		TO-263	45	

FIG.1: Maximum power dissipation versus RMS on-state current

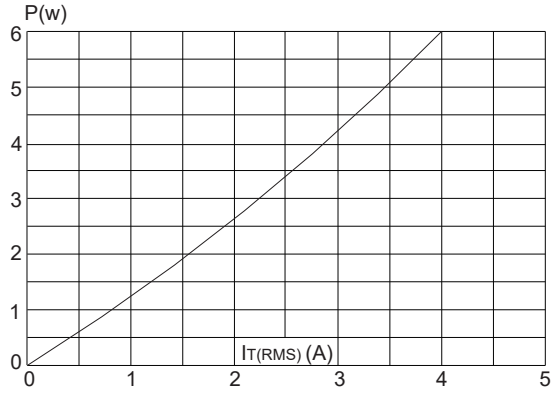


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35 μ m)

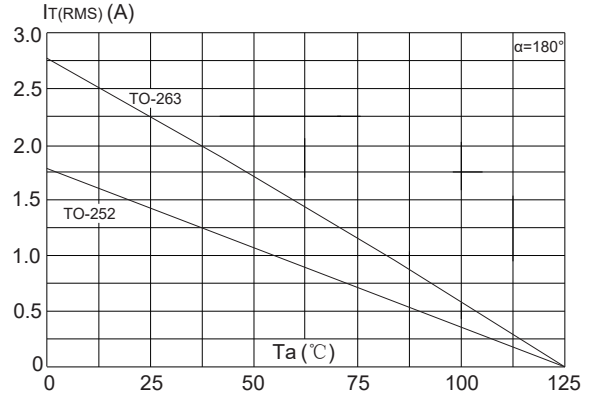


FIG.3: Surge peak on-state current versus number of cycles

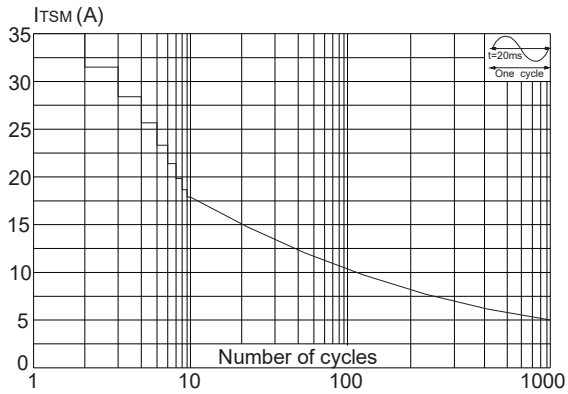


FIG.4: On-state characteristics (maximum values)

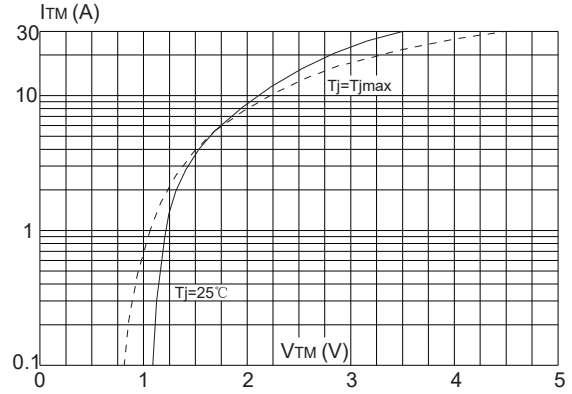


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t (I - II -III: $dI/dt < 50\text{A}/\mu\text{s}$; IV: $dI/dt < 10\text{A}/\mu\text{s}$)

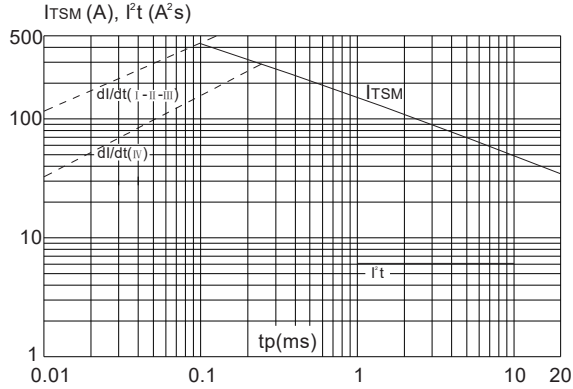


FIG.7: Relative variations of holding current versus junction temperature

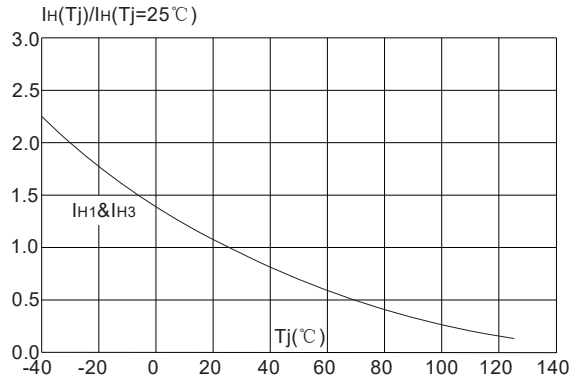


FIG.6: Relative variations of gate trigger current versus junction temperature

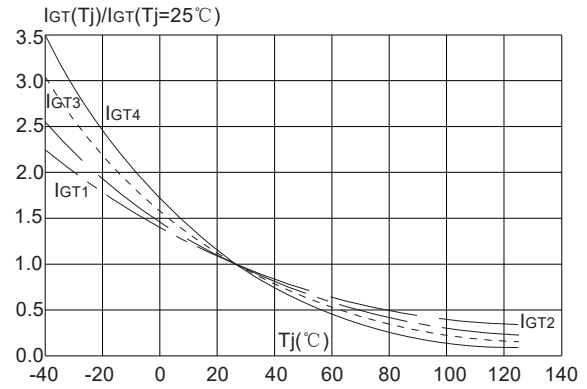
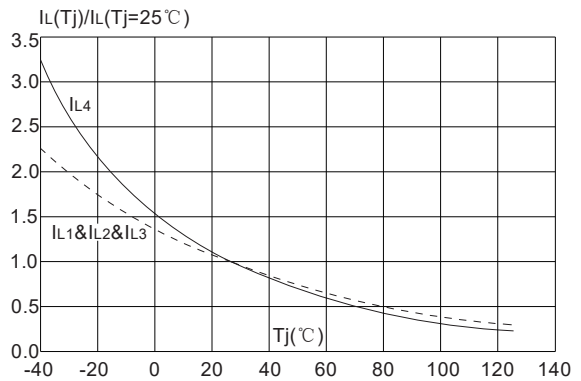


FIG.8: Relative variations of latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

